

Silicon NPN Power Transistors

BU426 BU426A

DESCRIPTION

- With TO-3PN package
- High voltage ,high speed

APPLICATIONS

- Intended for use in switching-mode color TV supply systems

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

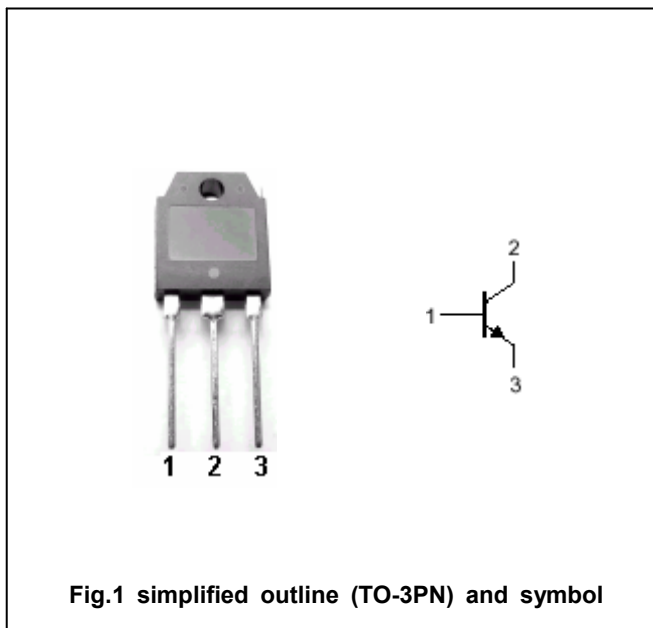


Fig.1 simplified outline (TO-3PN) and symbol

Absolute maximum ratings (Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	BU426	800	V
		BU426A	900	
V _{CEO}	Collector-emitter voltage	BU426	375	V
		BU426A	400	
V _{EBO}	Emitter-base voltage	Open collector	10	V
I _C	Collector current (DC)		6	A
I _{CM}	Collector current (Pulse)		8	A
I _B	Base current		3	A
P _C	Collector power dissipation	T _C =25°C	113	W
T _j	Junction temperature		150	°C
T _{stg}	Storage temperature		-65~150	°C

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CE0(SUS)}	Collector-emitter sustaining voltage	BU426	I _C =100mA; I _B =0			V
		BU426A				
V _{CEsat-1}	Collector-emitter saturation voltage	I _C =2.5A; I _B =0.5A			1.5	V
V _{CEsat-2}	Collector-emitter saturation voltage	I _C =4A; I _B =1.25A			3.0	V
V _{BEsat-1}	Base-emitter saturation voltage	I _C =2.5A; I _B =0.5A			1.4	V
V _{BEsat-2}	Base-emitter saturation voltage	I _C =4A; I _B =1.25A			1.6	V
I _{CES}	Collector cut-off current	BU426	V _{CE} =800V; V _{BE} =0 T _C =125°C		1.0 2.0	mA
		BU426A				
I _{EBO}	Emitter cut-off current	V _{EB} =10V; I _C =0			10	mA
h _{FE}	DC current gain	I _C =0.6A; V _{CE} =5V		30	60	

Switching times

t _{on}	Turn-on time	I _C =2.5A; V _{CC} =250V I _{B1} =0.5A			0.5	μs
t _{stg}	Storage time	I _C =2.5A; V _{CC} =250V I _{B1} =0.5A; I _{B2} =-1A			3.5	μs
t _f	Fall time				0.5	μs

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
R _{th j-c}	Thermal resistance from junction to case	1.1	°C/W

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PACKAGE OUTLINE

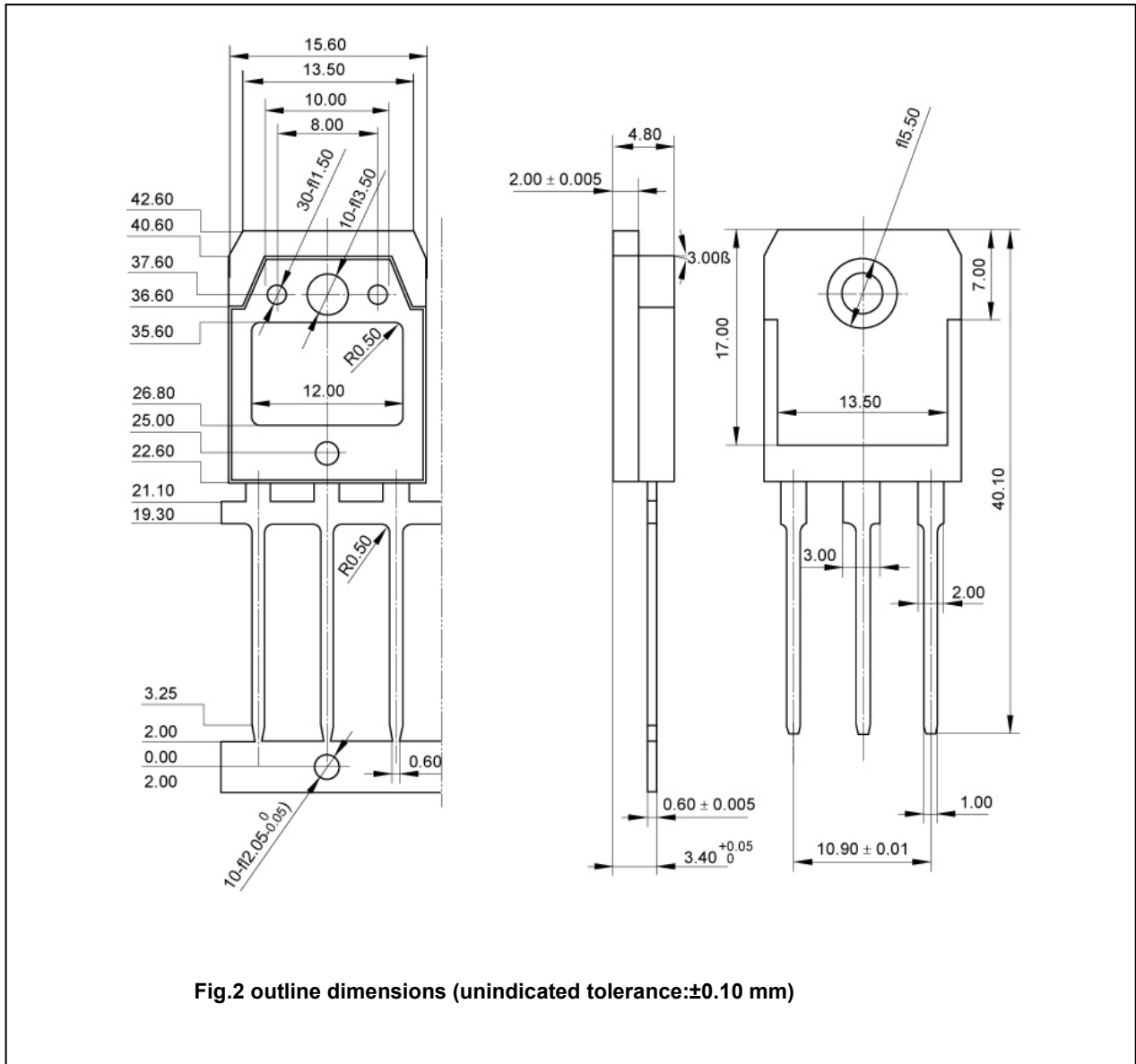


Fig.2 outline dimensions (unindicated tolerance:±0.10 mm)